Product data sheet

1. General description

Ultrafast power diode in a TO220F-2L plastic package.

2. Features and benefits

- Fast switching
- Isolated plastic package
- Low leakage current
- · Low reverse recovery current
- Low thermal resistance
- · Reduces switching losses in associated MOSFET or IGBT

3. Applications

- · Active PFC in air conditioner
- · High frequency switched-mode power supplies
- Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes		Values		Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage				650		V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; Fig. 1; Fig. 2; Fig. 3			20		А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; square-wave pulse			40		Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		250 275		Α	
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse				Α	
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V_{F}	forward voltage	I _F = 20 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.65	2.20	V
		I _F = 20 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.25	1.80	V
Dynamic	characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 200 \text{ A/µs}$; $T_j = 25 \text{ °C}$; Fig. 7		-	23	-	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	А	anode	000	K — A 001aaa020
mb	n.c.	mounting base; isolated		001aaa020

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number		Small packing quantity	Package version	Package issue date
BYV20MX-650P	TO220F-2L	BYV20MX-650PQ	Tube	50	TO220Fd-2L	02-Aug-2022

7. Marking

Table 4. Marking codes

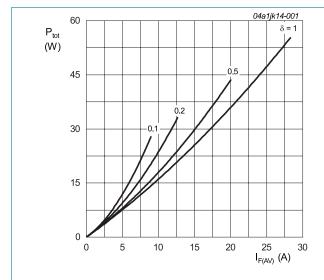
Type number	Marking codes
BYV20MX-650P	BYV20MX 650P

8. Limiting values

Table 5. Limiting values

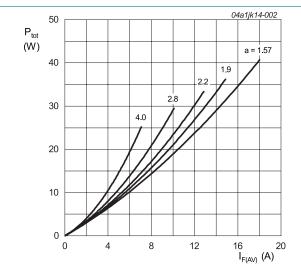
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{RRM}	repetitive peak reverse voltage			650	V
V_{RWM}	crest working reverse voltage			650	V
V_R	reverse voltage	DC		650	V
I _{F(AV)}	average forward current	δ = 0.5 ; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		20	Α
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; square-wave pulse		40	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		250	Α
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		275	А
T _{stg}	storage temperature			-65 to 175	°C
T _j	junction temperature			-65 to 175	°C



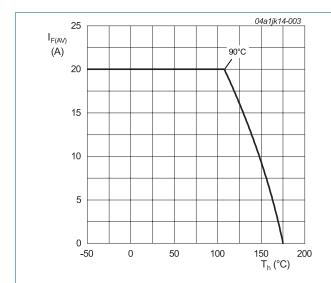
$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_o &= 1.419 \text{ V; } R_s = 0.0189 \text{ } \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 1.419 V; R_s = 0.0189 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values



square waveform; δ = 1 Fig. 3. Forward current as a function of heatsink temperature; typical values

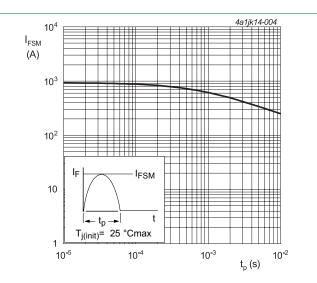
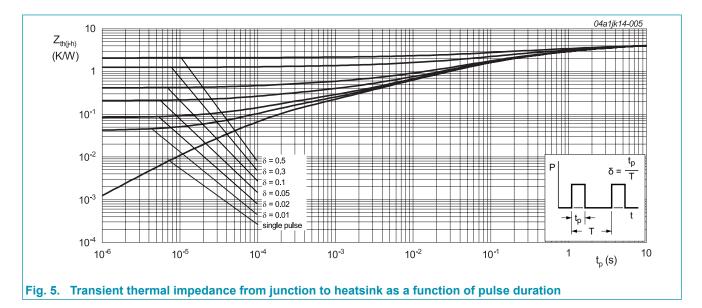


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; Fig. 5		-	-	4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W



10. Isolation characteristics

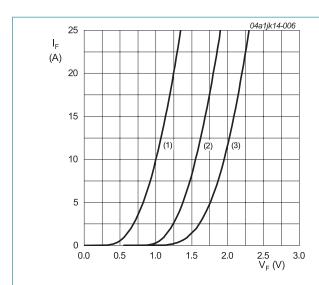
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free		-	-	2500	V
C _{isol}	isolation capacitance	f = 1 MHz; from cathode to external heatsink		-	10	-	pF

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V_{F}	forward voltage	I _F = 20 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.65	2.20	V
		I _F = 20 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.25	1.80	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C		-	0.2	30	μA
		V _R = 650 V; T _j = 150 °C		-	0.05	-	mA
Dynamic	characteristics						
Q _r reverse char	reverse charge	$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	125	-	nC
		$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	500	-	nC
t _{rr}	reverse recovery time	$I_F = 0.5 \text{ A}; I_{rr} = 0.25 \text{ A}; I_R = 1 \text{ A};$ $T_j = 25 \text{ °C}; Fig. 7$		-	36	-	ns
		$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig.		-	23	-	ns
		$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	65	-	ns
		$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	100	-	ns
I _{RM}	peak reverse recovery current	$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	4.5	-	А
		$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	9.5	-	А
E _{as}	non-repetitive avalanche energy	T _{j(init)} = 25 °C		25	-	-	mJ



 V_o = 1.419 V; R_s = 0.0189 Ω (1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values (3) T_j = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage

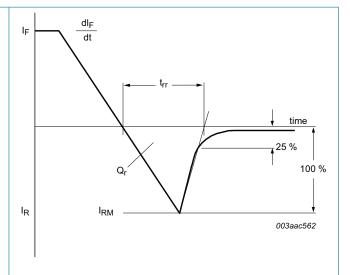
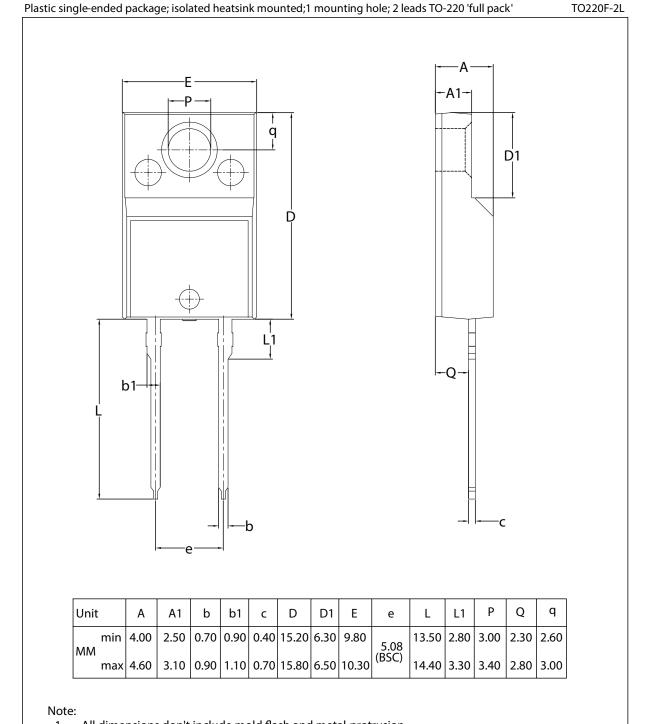


Fig. 7. Reverse recovery definitions; ramp recovery

12. Package outline



1. All dimensions don't include mold flash and metal protrusion.

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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BYV20MX-650P

Ultrafast power diode

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